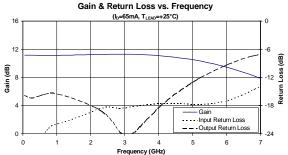


### **Product Description**

Sirenza Microdevices' SNA-686 is a GaAs HBT MMIC Amplifier housed in a low-cost, surface-mountable plastic package. The heterojunction increases breakdown voltage and minimizes leakage current between junctions. Cancellation of emitter junction non-linearities results in higher suppression of intermodulation products.

The use of an external resistor allows for bias flexibility and stability. These unconditionally stable amplifiers are designed for use as general purpose 50 ohm gain blocks.

Also available in chip form (SNA-600), its small size (0.38mm  $\times$  0.38mm) and gold metallization make it an ideal choice for use in hybrid circuits.



# **SNA-686**

# DC-6 GHz, Cascadable GaAs HBT MMIC Amplifier

Not Recommended for New Designs See Application Note AN-019 for Alternates



#### **Product Features**

- Patented GaAs HBT Technology
- Cascadable 50 Ohm Gain Block
- 34 dBm Output IP3 @ 850 MHz
- Operates From Single Supply
- Low Cost Surface Mount Plastic Package

# **Applications**

• Cellular, PCS, CDPD, Wireless Data, SONET

Symbol	Parameter	Frequency	Units	Min.	Тур.	Max.
P <sub>1dB</sub>	Output Power at 1dB Compression	850 MHz 1950 MHz 2400 MHz	dBm dBm dBm	15.7	17.6 17.7 17.4	
IP <sub>3</sub>	Third Order Intercept Point	850 MHz 1950 MHz 2400 MHz	dBm dBm dBm	29.1	34.0 32.1 30.0	
S <sub>21</sub>	Small Signal Gain	850 MHz 1950 MHz 2400 MHz	dB dB dB	10.0 10.1	11.1 11.2 11.3	12.2 12.3
Bandwidth	(Determined by S <sub>11</sub> , S <sub>22</sub> Values)		MHz		6000	
VSWR <sub>IN</sub>	Input VSWR	DC-6000 MHz	-		1.3:1	
VSWR <sub>OUT</sub>	Output VSWR	DC-6000 MHz	-		1.4:1	
S <sub>12</sub>	Reverse Isolation	850 MHz 1950 MHz 2400 MHz	dB dB dB		16.3 16.5 16.6	
NF	Noise Figure	1950 MHz	dB		7.3	8.8
V <sub>D</sub>	Device Operating Voltage		V	5.0	5.3	5.6
I <sub>D</sub>	Device Operating Current		I	58	65	72
R <sub>TH</sub> , j-l	Thermal Resistance (junction - lead)		° C/W		261	

Test Conditions:  $V_S = 8 \text{ V}$   $I_D = 65 \text{ mA Typ.}$  OIP<sub>3</sub> Tone Spacing = 1 MHz, Pout per tone = 0 dBm  $R_{BIAS} = 43 \text{ Ohms}$   $R_{BIAS} = 43 \text{ Ohms}$   $R_{CONS} = 25 \text{ o}$   $R_{CONS} = 27 \text{ o}$  OIP<sub>3</sub> Tone Spacing = 1 MHz, Pout per tone = 0 dBm  $R_{CONS} = 27 \text{ o}$  OIP<sub>3</sub> Tone Spacing = 1 MHz, Pout per tone = 0 dBm  $R_{CONS} = 27 \text{ o}$  OIP<sub>3</sub> Tone Spacing = 1 MHz, Pout per tone = 0 dBm  $R_{CONS} = 27 \text{ o}$  OIP<sub>3</sub> Tone Spacing = 1 MHz, Pout per tone = 0 dBm  $R_{CONS} = 27 \text{ o}$  OIP<sub>3</sub> Tone Spacing = 1 MHz, Pout per tone = 0 dBm  $R_{CONS} = 27 \text{ o}$  OIP<sub>3</sub> Tone Spacing = 1 MHz, Pout per tone = 0 dBm  $R_{CONS} = 27 \text{ o}$  OIP<sub>3</sub> Tone Spacing = 1 MHz, Pout per tone = 0 dBm  $R_{CONS} = 27 \text{ o}$  OIP<sub>3</sub> Tone Spacing = 1 MHz, Pout per tone = 0 dBm  $R_{CONS} = 27 \text{ o}$  OIP<sub>3</sub> Tone Spacing = 1 MHz, Pout per tone = 0 dBm  $R_{CONS} = 27 \text{ o}$  OIP<sub>3</sub> Tone Spacing = 1 MHz, Pout per tone = 0 dBm  $R_{CONS} = 27 \text{ o}$  OIP<sub>3</sub> Tone Spacing = 1 MHz, Pout per tone = 0 dBm  $R_{CONS} = 27 \text{ o}$  OIP<sub>3</sub> Tone Spacing = 1 MHz, Pout per tone = 0 dBm  $R_{CONS} = 27 \text{ o}$  OIP<sub>3</sub> Tone Spacing = 1 MHz, Pout per tone = 0 dBm  $R_{CONS} = 27 \text{ o}$  OIP<sub>3</sub> Tone Spacing = 1 MHz, Pout per tone = 0 dBm  $R_{CONS} = 27 \text{ o}$  OIP<sub>3</sub> Tone Spacing = 1 MHz, Pout per tone = 0 dBm  $R_{CONS} = 27 \text{ o}$  OIP<sub>3</sub> Tone Spacing = 1 MHz, Pout per tone = 0 dBm  $R_{CONS} = 27 \text{ o}$  OIP<sub>3</sub> Tone Spacing = 1 MHz, Pout per tone = 0 dBm  $R_{CONS} = 27 \text{ o}$  OIP<sub>3</sub> Tone Spacing = 1 MHz, Pout per tone = 0 dBm  $R_{CONS} = 27 \text{ o}$  OIP<sub>3</sub> Tone Spacing = 1 MHz, Pout per tone = 0 dBm  $R_{CONS} = 27 \text{ o}$  OIP<sub>3</sub> Tone Spacing = 1 MHz, Pout per tone = 0 dBm  $R_{CONS} = 27 \text{ o}$  OIP<sub>3</sub> Tone Spacing = 1 MHz, Pout per tone = 0 dBm  $R_{CONS} = 27 \text{ o}$  OIP<sub>3</sub> Tone Spacing = 1 MHz, Pout per tone = 0 dBm  $R_{CONS} = 27 \text{ o}$  OIP<sub>3</sub> Tone Spacing = 1 MHz, Pout per tone = 0 dBm  $R_{CONS} = 27 \text{ o}$  OIP<sub>3</sub> Tone Spacing = 1 MHz, Pout per tone = 0 dBm  $R_{CONS} = 27 \text{ o}$  OIP<sub>3</sub> Tone Spacing = 1 MHz, Pout per tone = 1 MHz, Pout per tone = 1 MHz, Pout per tone = 1

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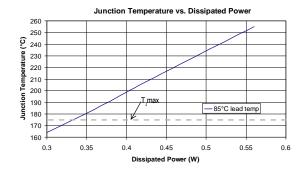


#### Typical RF Performance at Key Operating Frequencies

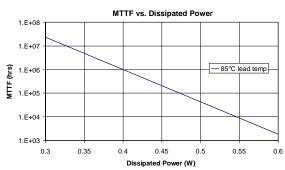
			Frequency (MHz)					
Symbol	Parameter	Unit	100	500	850	1950	2400	3500
G	Small Signal Gain	dB	11.1	11.1	11.1	11.2	11.3	11.3
OIP <sub>3</sub>	Output Third Order Intercept Point	dBm		35.0	34.0	32.1	30.0	
P <sub>1dB</sub>	Output Power at 1dB Compression	dBm		17.5	17.6	17.7	17.4	
IRL	Input Return Loss	dB	29.5	25.2	22.3	19.6	18.4	17.9
ORL	Output Return Loss	dB	16.0	15.9	15.3	17.8	19.6	22.2
S <sub>12</sub>	Reverse Isolation	dB	16.2	16.2	16.3	16.5	16.6	17.0
NF	Noise Figure	dB		7.2	7.3	7.3		
Test Conditions: $V_s = 8v$ $I_D = 65mA$ Typ. OIP3 Tone Spacing = 1 MHz, Pout per tone = 0 dBm $R_{ave} = 43 \text{ Ohms} \qquad T_v = 25^{\circ}\text{C} \qquad Z_v = Z_v = 50 \text{ Ohms}$								

Absolute Maximum Ratings	Parameter	Absolute Limit
Absolute Maximum Ratings	Max. Device Current (I <sub>D</sub> )	120 mA
Operation of this device beyond any one of these limits may	Max. Device Voltage (V <sub>D</sub> )	7 V
cause permanent damage. For reliable continuus operation, the device voltage and current must not exceed the maximum	Max. RF Input Power	+16 dBm
operating values specified in the table on page one.	Max. Junction Temp. (T <sub>J</sub> )	+175°C
Bias Conditions should also satisfy the following expression:	Operating Temp. Range (T <sub>L</sub> )	-40°C to +85°C

**NOTE:** While the SNA-686 can be operated at different bias currents, 65 mA is the recommended bias for lower junction temperature and longer life. This reflects typical operating conditions which we have found to be an optimal balance between high IP3 and MTTF. In general, MTTF is improved to more than 100,000 hours when biasing at 65 mA and operating up to 85°C ambient temperature.



 $I_D V_D < (T_J - T_L) / R_{TH}, j-1$ 



+150°C

Max. Storage Temp.

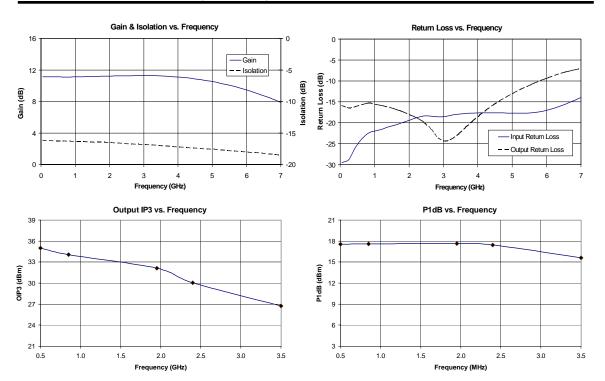
522 Almanor Ave., Sunnyvale, CA 94085

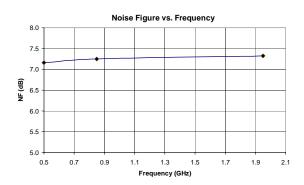
Phone: (800) SMI-MMIC





# Typical RF Performance ( $V_{DS} = 5.3V$ , $I_{DS} = 65mA$ , $T_{LEAD} = 25^{\circ}$ C)

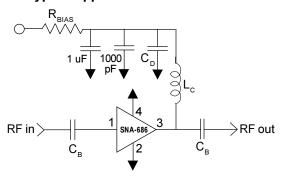


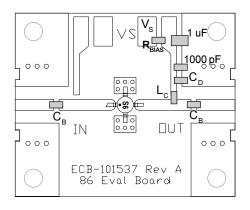




# **SNA-686 DC-6GHz Cascadable MMIC Amplifier**

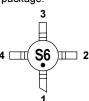
#### **Typical Application Circuit**





#### Part Identification Marking

The part will be marked with an "S6" designator on the top surface of the package.





#### **Application Circuit Element Values**

Reference		Frequency (Mhz)					
Designator	500	850	1950	2400	3500		
C <sub>B</sub>	220 pF	100 pF	68 pF	56 pF	39 pF		
C <sub>D</sub>	100 pF	68 pF	22 pF	22 pF	15 pF		
L <sub>c</sub>	68 nH	33 nH	22 nH	18 nH	15 nH		

Recommended Bias Resistor Values for $I_D$ =65mA $R_{BIAS}$ =( $V_S$ - $V_D$ ) / $I_D$				
Supply Voltage(V <sub>s</sub> )	8 V	9 V	12 V	15 V
R <sub>BIAS</sub>	43 Ω	56 Ω	100 Ω	150 Ω

Note: R<sub>BIAS</sub> provides DC bias stability over temperature.

#### **Mounting Instructions**

- 1. Use a large ground pad area under device pins 2 and 4 with many plated through-holes as shown.
- 2. We recommend 1 or 2 ounce copper. Measurements for this data sheet were made on a 31 mil thick FR-4 board with 1 ounce copper on both sides.

Pin#	Function	Description
1	RF IN	RF input pin. This pin requires the use of an external DC blocking capacitor chosen for the frequency of operation.
2, 4	GND	Connection to ground. For optimum RF performance, use via holes as close to ground leads as possible to reduce lead inductance.
3	RF OUT/ BIAS	RF output and bias pin. DC voltage is present on this pin, therefore a DC blocking capacitor is necessary for proper operation.

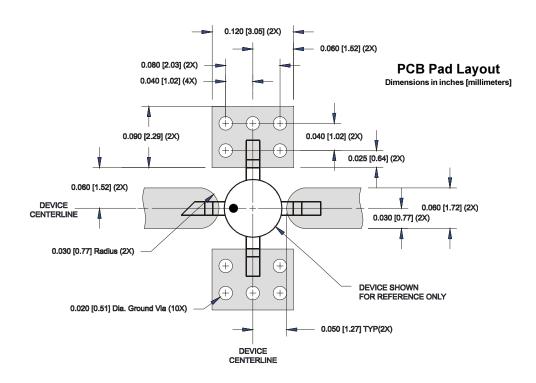
#### **Part Number Ordering Information**

Part Number	Reel Size	Devices/Reel
SNA-686	7"	1000

522 Almanor Ave., Sunnyvale, CA 94085 Phone: (800) SMI-MMIC http://www.sirenza.com 4







# **Nominal Package Dimensions**

Dimensions in inches [millimeters]

Refer to drawing posted at www.sirenza.com for tolerances.

